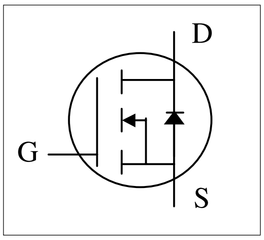
AP9466GS

RoHS-compliant Product

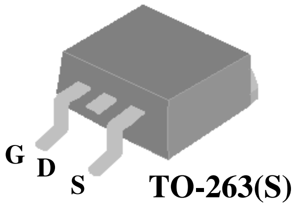
Advanced Power Electronics Corp.

N-CHANNEL ENHANCEMENT MODE
POWER MOSFET

- ▼ **Low On-resistance**
- ▼ **Single Drive Requirement**
- ▼ **Fast Switching Characteristics**



BV_{DSS}	40V
$R_{DS(ON)}$	13.5mΩ
I_D	40A



Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-263 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	25	A
I_{DM}	Pulsed Drain Current[1]	150	A
P_D@T_C=25℃	Total Power Dissipation	36.7	W
	Linear Derating Factor	0.29	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter		Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max.	3.4	℃/W
Rthj-a	Thermal Resistance Junction-ambient	Max.	62	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	40	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=26A	-	-	13.5	mΩ
		V_{GS}=4.5V, I_D=16A	-	-	21	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=26A	-	24.5	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=40V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current (T_j=150°C)	V_{DS}=32V ,V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}= ±20V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=26A	-	13.5	22	nC
Q_{gs}	Gate-Source Charge	V_{DS}=32V	-	2.6	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	9.4	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=20V	-	7	-	ns
t_r	Rise Time	I_D=26A	-	73	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=10V	-	20	-	ns
t_f	Fall Time	R_D=0.77Ω	-	8	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	800	1280	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	170	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	140	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.3	2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=26A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	I_S=20A, V_{GS}=0V,	-	27	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/µs	-	20	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

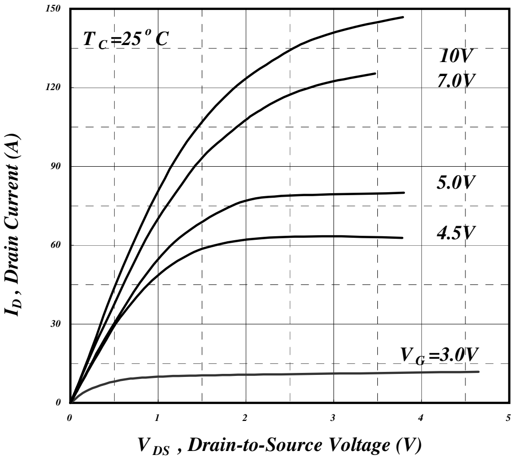


Fig 1. Typical Output Characteristics

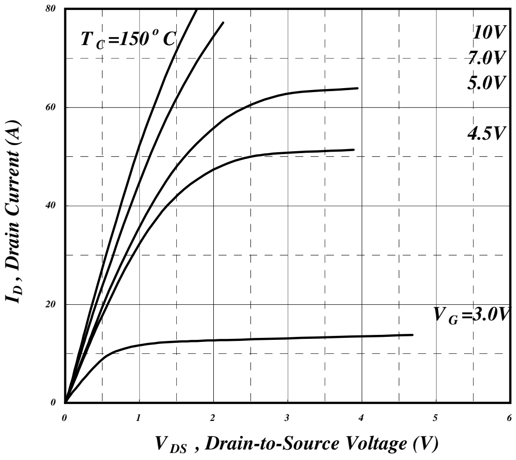


Fig 2. Typical Output Characteristics

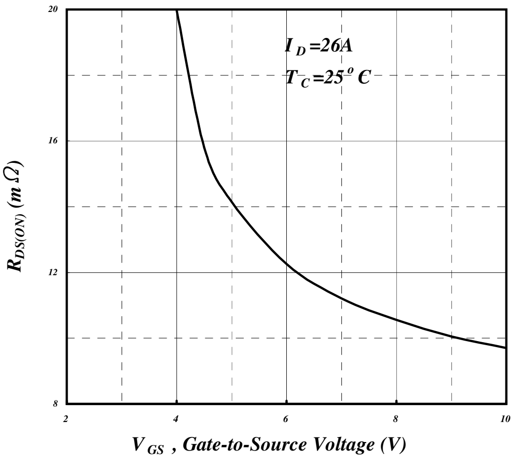


Fig 3. On-Resistance v.s. Gate Voltage

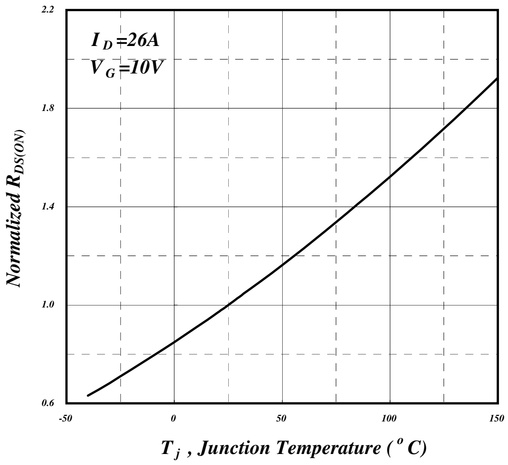


Fig 4. Normalized On-Resistance v.s. Junction Temperature

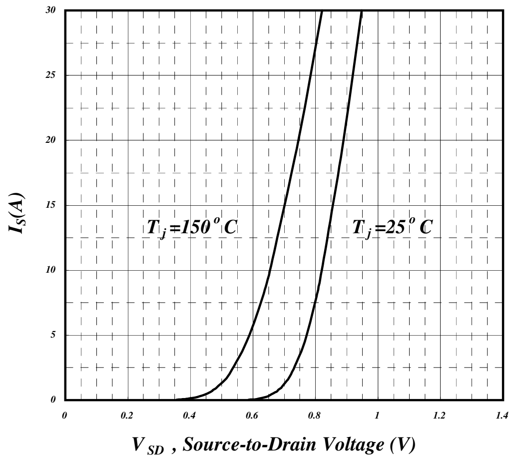


Fig 5. Forward Characteristic of Reverse Diode

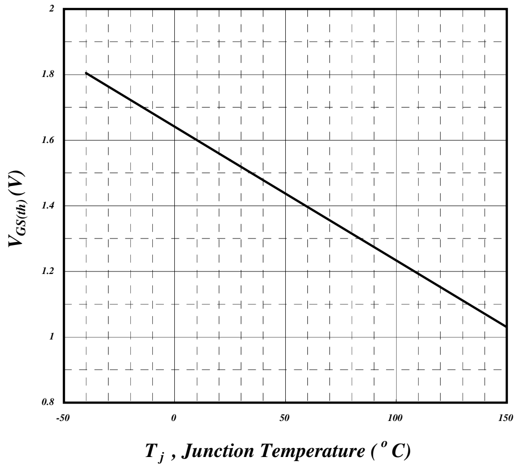


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

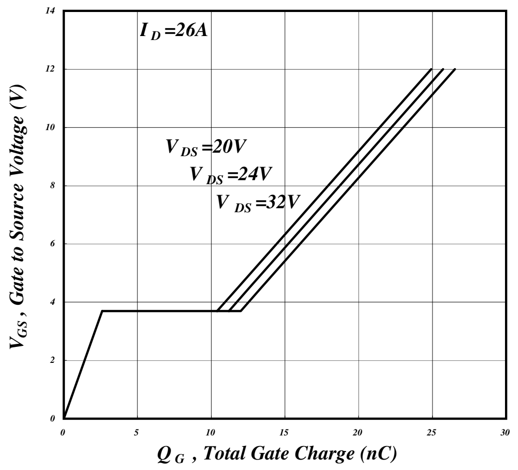


Fig 7. Gate Charge Characteristics

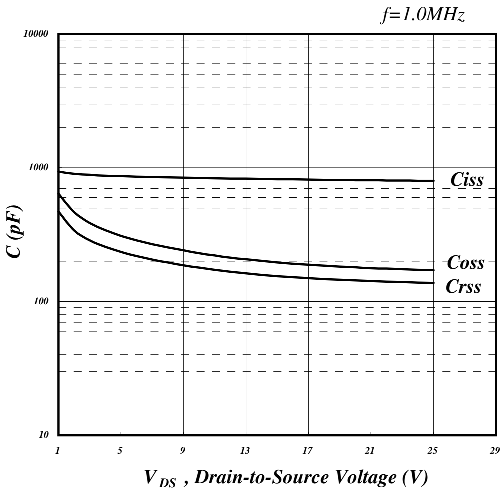


Fig 8. Typical Capacitance Characteristics

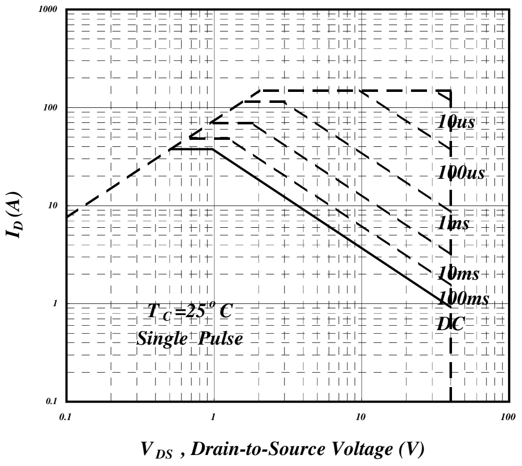


Fig 9. Maximum Safe Operating Area

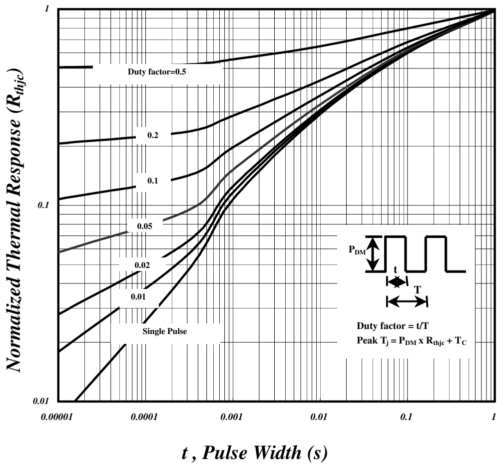


Fig 10. Effective Transient Thermal Impedance

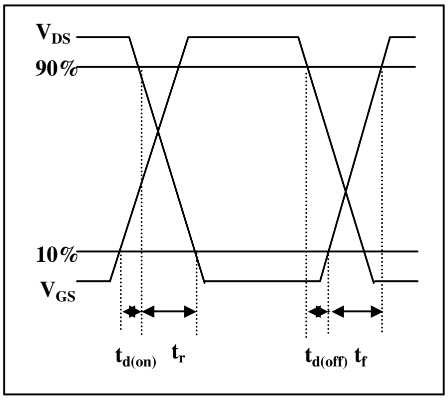


Fig 11. Switching Time Waveform

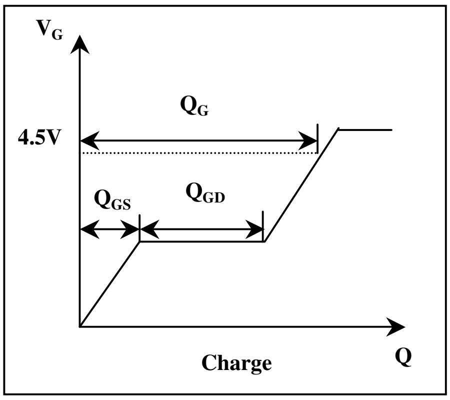
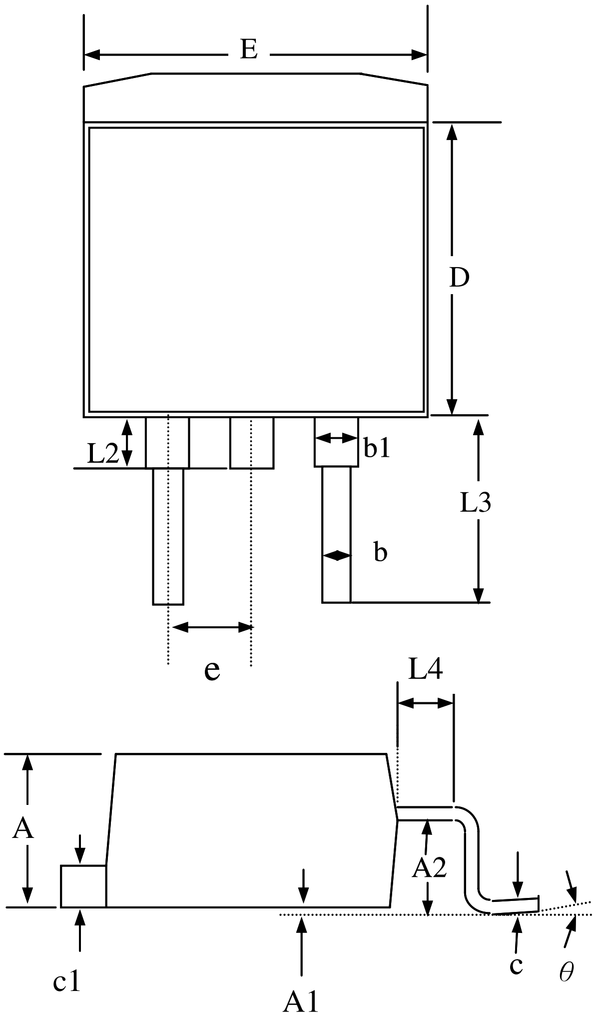


Fig 12. Gate Charge Waveform

Package Outline : TO-263

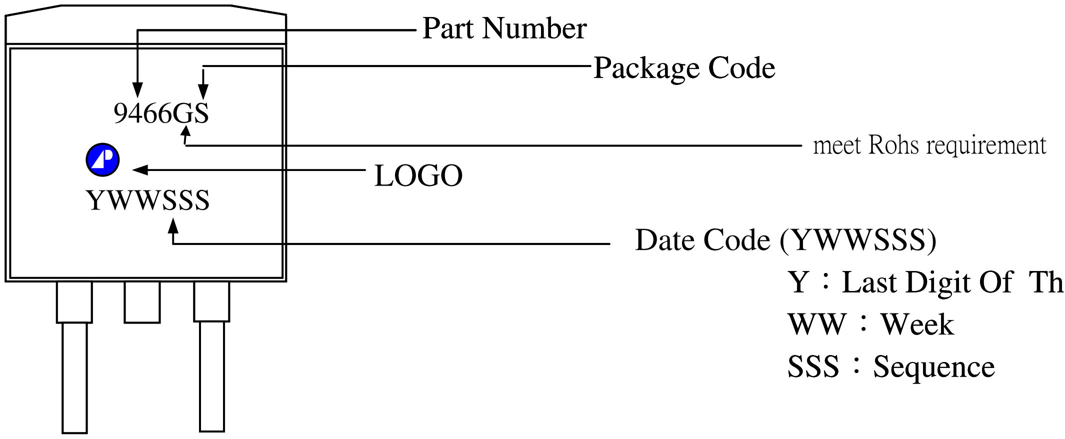


SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.75	5.20
A1	0.00	0.15	0.30
A2	2.20	2.45	2.70
b	0.70	0.90	1.10
b1	1.07	1.27	1.47
c	0.30	0.45	0.60
c1	1.15	1.30	1.45
D	8.30	8.90	9.40
E	9.70	10.10	10.50
e	2.04	2.54	3.04
L2	-----	1.50	-----
L3	4.50	4.90	5.30
L4	-----	1.50	----

1.All Dimensions Are in Millimeters.

2.Dimension Does Not Include Mold Protrusions.

Part Marking Information & Packing : TO-263



Y : Last Digit Of The Year

WW : Week

SSS : Sequence